

MBRB40200CT SCHOTTKY RECTIFIER

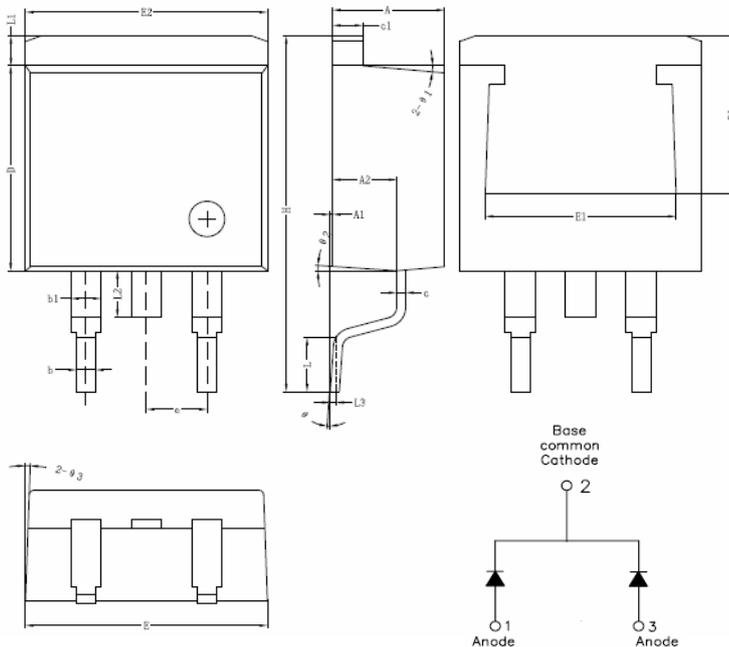
Applications:

- Switching power supply
- Converters
- Free-Wheeling diodes
- Reverse battery protection

Features:

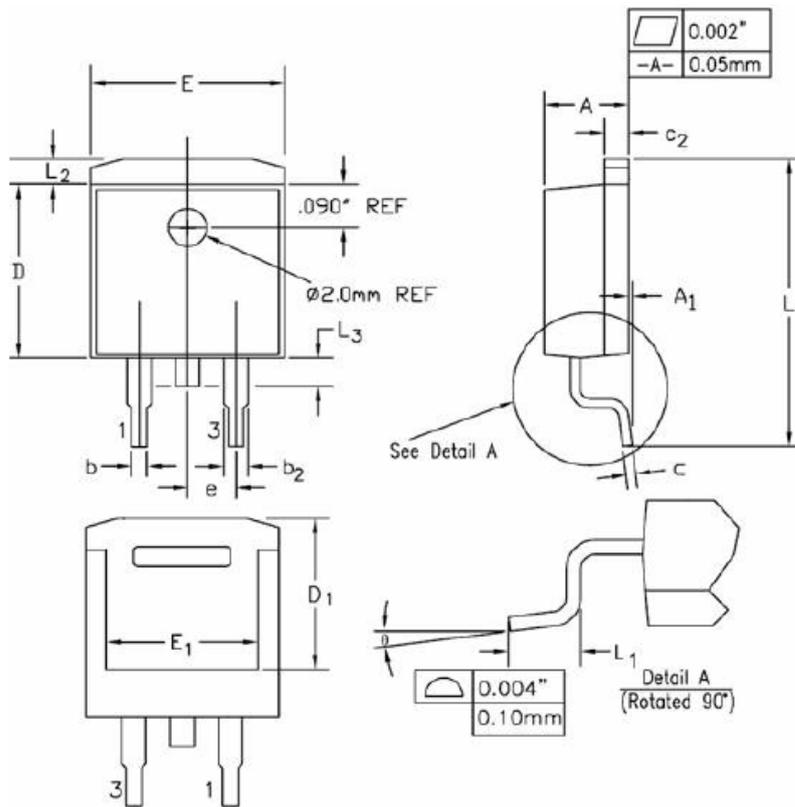
- 150°C T_J operation
- Center tap configuration
- Low forward voltage drop
- High purity, high temperature epoxy encapsulation for enhanced mechanical strength and moisture resistance
- High frequency operation
- Guard ring for enhanced ruggedness and long term reliability
- This is a Pb – Free Device
- All SMC parts are traceable to the wafer lot
- Additional testing can be offered upon request

Mechanical Dimensions (In Inches / mm):



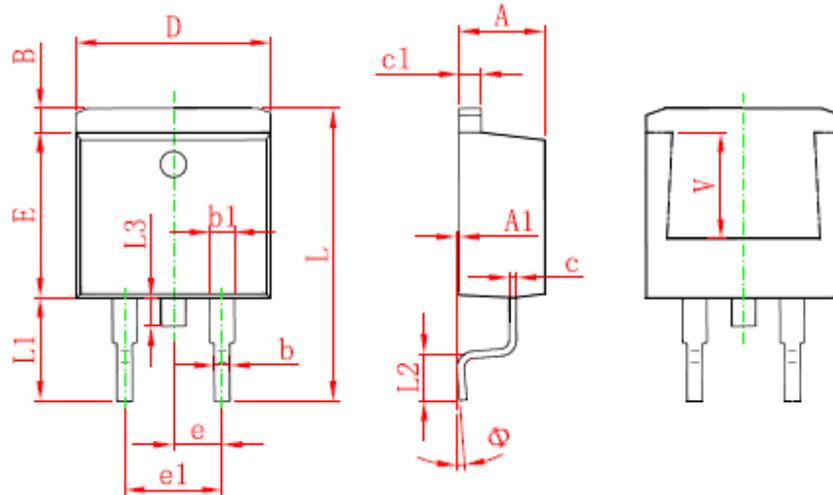
Symbol	Dimensions in millimeters		
	Min.	Typical	Max.
A	4.55	4.70	4.85
A1	0	0.10	0.25
A2	2.59	2.69	2.89
b	0.71	0.81	0.96
b1		1.27	
c	0.36	0.38	0.61
c1	1.17	1.27	1.37
D	8.55	8.70	8.85
D1	6.40		
E	10.01	10.16	10.31
E1	7.6		
E2	9.98	10.08	10.18
e		2.54	
H	14.6	15.1	15.6
L	2.00	2.30	2.70
L1	1.17	1.27	1.40
L2			2.20
L3		0.25BSC	
e	0	-	8°
e1		5°	
e2		4°	
e3		4°	

OPTION 1(HD)



SYMBOL	MILLIMETERS	
	MIN.	MAX.
A	4.32	4.57
A ₁	0	0.25
b	0.71	0.91
b ₂	1.15	1.40
c	0.46	0.61
c ₂	1.22	1.40
D	8.89	9.40
D ₁	8.01	8.23
E	10.04	10.28
E ₁	7.88	8.08
e	2.54 BSC.	
L	14.73	15.75
L ₁	2.29	2.79
L ₂	1.15	1.39
L ₃	1.27	1.77
θ	0°	8°

OPTION 2(MX)



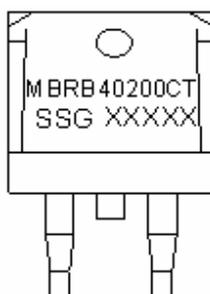
Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	4.470	4.670	0.176	0.184
A1	0.000	0.150	0.000	0.006
B	1.120	1.420	0.044	0.056
b	0.710	0.910	0.028	0.036
b1	1.170	1.370	0.046	0.054
c	0.310	0.530	0.012	0.021
c1	1.170	1.370	0.046	0.054
D	10.010	10.310	0.394	0.406
E	8.500	8.900	0.335	0.350
e	2.540 TYP.		0.100 TYP.	
e1	4.980	5.180	0.196	0.204
L	14.940	15.500	0.588	0.610
L1	4.950	5.450	0.195	0.215
L2	2.340	2.740	0.092	0.108
L3	1.300	1.700	0.051	0.067
Φ	0°	8°	0°	8°
V	5.600 REF.		0.220 REF.	

OPTION 3(CJ)

D² PAK

Marking Diagram:

Where XXXXX is YYWWL



MBR	= Device Type
B	= Package type
40	= Forward Current (40A)
200	= Reverse Voltage (200V)
CT	= Configuration
SSG	= SSG
YY	= Year
WW	= Week
L	= Lot Number

Cautions: Molding resin
 Epoxy resin UL:94V-0

Ordering Information:

Device	Package	Shipping
MBRB40200CT	D ² PAK (Pb-Free)	800pcs / reel

For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification.

Maximum Ratings:

Characteristics	Symbol	Condition	Max.	Units
Peak Inverse Voltage	V_{RWM}	-	200	V
Max. Average Forward	$I_{F(AV)}$	50% duty cycle @ $T_C = 110^\circ\text{C}$, rectangular wave form	20(per leg)	A
			40(Per device)	
Max. Peak One Cycle Non-Repetitive Surge Current (per leg)	I_{FSM}	8.3 ms, half Sine pulse	396	A

Electrical Characteristics:

Characteristics	Symbol	Condition	Max.	Units
Max. Forward Voltage Drop (per leg)*	V _{F1}	@ 20A, Pulse, T _J = 25 °C	0.90	V
	V _{F2}	@ 20 A, Pulse, T _J = 125 °C	0.80	V
Max. Reverse Current at DC condition (per leg)	I _{R1}	@V _R = rated V _R T _J = 25 °C	1.0	mA
Max. Reverse Current (per leg)*	I _{R2}	@V _R = rated V _R T _J = 125 °C	11.0	mA
Max. Junction Capacitance (per leg)	C _T	@V _R = 5V, T _C = 25 °C f _{SIG} = 1MHz	450	pF
Typical Series Inductance (per leg)	L _S	Measured lead to lead 5 mm from package body	8.0	nH
Max. Voltage Rate of Change	dv/dt	-	10,000	V/μs

* Pulse Width < 300μs, Duty Cycle <2%

Thermal-Mechanical Specifications:

Characteristics	Symbol	Condition	Specification	Units
Max. Junction Temperature	T _J	-	-55 to +150	°C
Max. Storage Temperature	T _{stg}	-	-55 to +150	°C
Maximum Thermal Resistance Junction to Case (per leg)	R _{θJC}	DC operation	2.0	°C/W
Approximate Weight	wt	-	1.85	g
Case Style	D2PAK			

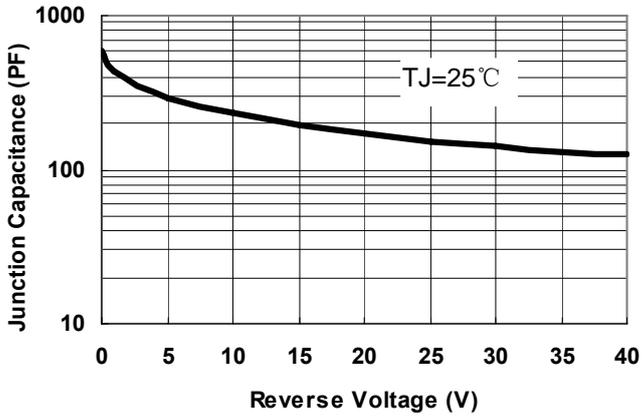


Fig.1-Typical Junction Capacitance

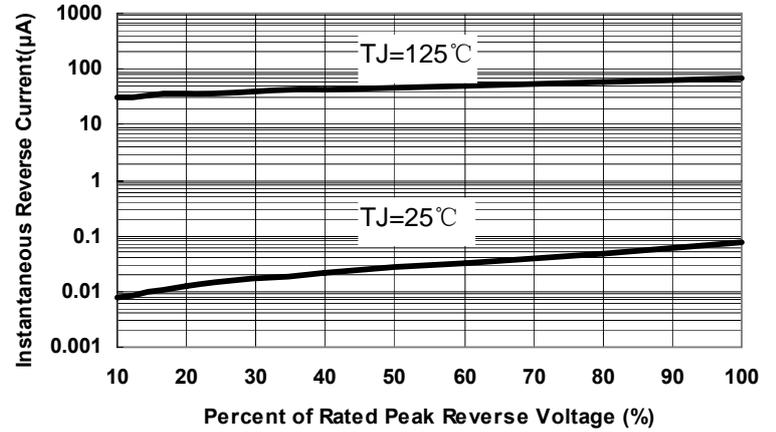


Fig.2-Typical Reverse Characteristics

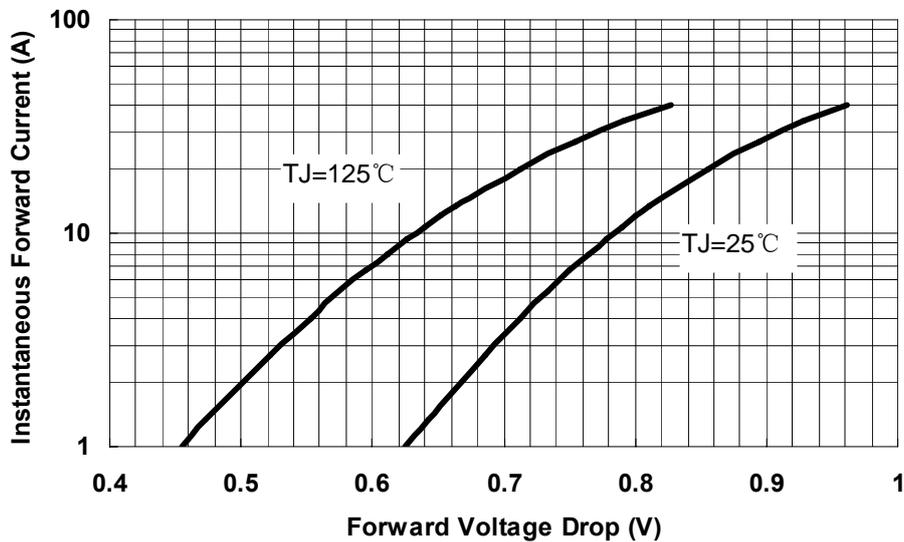


Fig.3-Typical Instantaneous Forward Voltage Characteristics

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